



# PerF≝T<sup>™</sup>Power Transistor

#### **FEATURES**

- Excellent FOM
- Reliability meets AEC-Q101 requirements
- Wettable flank leads for enhanced AOI
- 100% UIS and Rg tested
- 175°C operating junction temperature
- RoHS Compliant
- Halogen-free

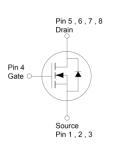
| KEY PERFORMANCE PARAMETERS |                       |       |      |  |
|----------------------------|-----------------------|-------|------|--|
| PARAMETER                  |                       | VALUE | UNIT |  |
| V <sub>DS</sub>            |                       | 100   | V    |  |
|                            | V <sub>GS</sub> = 10V | 17    | 0    |  |
| R <sub>DS(on)</sub> (max)  | V <sub>GS</sub> = 7V  | 20.4  | mΩ   |  |
| $Q_g$                      | V <sub>GS</sub> = 10V | 11    | nC   |  |



#### **APPLICATIONS**

- Solenoid and motor drivers
- DC-DC converters
- Load Switch
- SMPS





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

| ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted) |                        |                                   |              |      |  |
|---|------------------------|-----------------------------------|--------------|------|--|
| PARAMETER   |                        | SYMBOL                            | LIMIT        | UNIT |  |
| Drain-Source Voltage  |                        | $V_{DS}$                          | 100          | V    |  |
| Gate-Source Voltage   |                        | V <sub>G</sub> S                  | ±20          | V    |  |
| Continuous Drain Current  | $T_C = 25^{\circ}C$    |                                   | 50           |      |  |
|   | Tc = 100°C             | ID                                | 36           | Α    |  |
|   | $T_A = 25^{\circ}C$    |                                   | 9            |      |  |
| Pulsed Drain Current (Note 1)   |                        | I <sub>DM</sub>                   | 200          | Α    |  |
| Single Pulse Avalanche Current (Note 2)                                 |                        | las                               | 11.3         | Α    |  |
| Single Pulse Avalanche Energy (Note 2)                                  |                        | Eas                               | 19           | mJ   |  |
| Total Power Dissipation   | T <sub>C</sub> = 25°C  | 0                                 | 97           | W    |  |
|   | T <sub>C</sub> = 125°C | P <sub>D</sub>                    | 32           |      |  |
| Operating Junction and Storage Temperature Range                        |                        | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +175 | °C   |  |

| THERMAL PERFORMANCE                             |                  |       |      |  |
|---|------------------|-------|------|--|
| PARAMETER                                       | SYMBOL           | LIMIT | UNIT |  |
| Junction to Case Thermal Resistance             | Rejc             | 1.54  | °C/W |  |
| Junction to Ambient Thermal Resistance (Note 3) | R <sub>ÐJA</sub> | 50    | °C/W |  |

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#### Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 0.3mH,  $V_{GS}$  = 10V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C.
- 3. Device on a PCB FR4 with 1 in<sup>2</sup> (single layer, 2 oz thickness) copper area for drain connection.



| PARAMETER                         | CONDITIONS   | SYMBOL              | MIN | TYP | MAX  | UNIT |
|-----------------------------------|--|---------------------|-----|-----|------|------|
| Static                            |  |                     |     |     |      |      |
| Drain-Source Breakdown Voltage    | $V_{GS} = 0V$ , $I_D = 1mA$  | BV <sub>DSS</sub>   | 100 |     |      | V    |
| Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = 250 \mu A$                                     | V <sub>GS(TH)</sub> | 2.4 | 3   | 3.6  | V    |
| Gate Body Leakage                 | $V_{GS} = \pm 20V, V_{DS} = 0V$  | I <sub>GSS</sub>    |     |     | ±100 | nA   |
|                                   | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 100V                           | I <sub>DSS</sub>    |     |     | 1    | μA   |
| Drain-Source Leakage Current      | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 100V<br>T <sub>J</sub> = 125°C |                     |     |     | 100  |      |
| Drain-Source On-State Resistance  | V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A                            | _                   |     | 13  | 17   | mΩ   |
| (Note 4)                          | V <sub>GS</sub> = 7V, I <sub>D</sub> = 25A                             | R <sub>DS(on)</sub> |     | 16  | 20.4 |      |
| Forward Transconductance (Note 4) | $V_{DS} = 10V, I_D = 6.3A$   | <b>G</b> fs         |     | 26  |      | S    |
| Dynamic (Note 5)                  |  |                     |     |     |      | •    |
| Total Gate Charge                 | $V_{DS} = 50V, I_{D} = 9A,$<br>$V_{GS} = 7V$                           | $Q_g$               |     | 8.4 |      | nC   |
| Total Gate Charge                 |  | Qg                  |     | 11  |      |      |
| Gate-Source Charge                | $V_{DS} = 50V, I_{D} = 9A,$<br>$V_{GS} = 10V$                          | Q <sub>gs</sub>     |     | 3.6 |      | nC   |
| Gate-Drain Charge                 |  | Q <sub>gd</sub>     |     | 2.5 |      |      |
| Input Capacitance                 |  | Ciss                |     | 725 |      |      |
| Output Capacitance                | $V_{DS} = 60V$ , $V_{GS} = 0V$ ,                                       | Coss                |     | 148 |      | pF   |
| Reverse Transfer Capacitance      | f = 1.0MHz   | Crss                |     | 20  |      |      |
| Gate Resistance                   | f = 1.0MHz   | Rg                  |     | 1.7 |      | Ω    |
| Switching (Note 6)                |  |                     |     |     |      |      |
| Turn-On Delay Time                |  | t <sub>d(on)</sub>  |     | 7.9 |      |      |
| Turn-On Rise Time                 | $V_{DD} = 50V, R_G = 6\Omega,$ $I_D = 9A, V_{GS} = 10V$                | t <sub>r</sub>      |     | 19  |      |      |
| Turn-Off Delay Time               |  | t <sub>d(off)</sub> |     | 13  |      | ns   |
| Turn-Off Fall Time                |  | t <sub>f</sub>      |     | 21  |      |      |
| Source-Drain Diode                |  |                     |     |     |      |      |
| Forward Voltage (Note 4)          | I <sub>S</sub> = 25A, V <sub>GS</sub> = 0V                             | VsD                 |     |     | 1.1  | V    |
| Reverse Recovery Time             | Is = 9A,   | t <sub>rr</sub>     |     | 50  |      | ns   |
| Reverse Recovery Charge           | di/dt = 100A/µs  | Qrr                 | -   | 64  |      | nC   |

#### Notes:

- 4. Pulse test: Pulse Width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ .
- 5. Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

### **ORDERING INFORMATION**

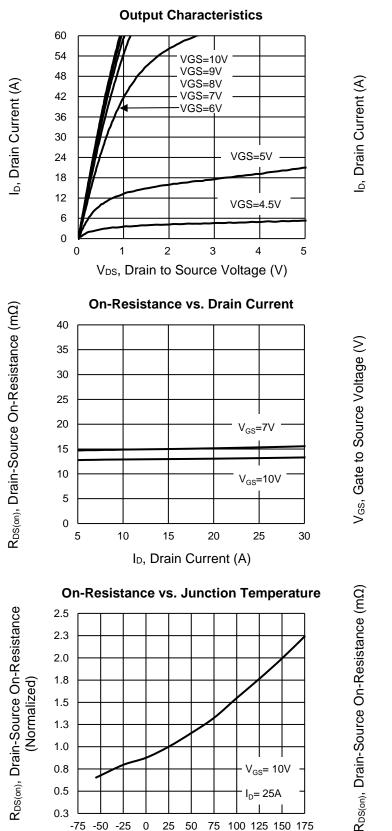
| ORDERING CODE    | PACKAGE | PACKING             |
|------------------|---------|---------------------|
| TSM170NH10CR RLG | PDFN56U | 2,500pcs / 13" Reel |



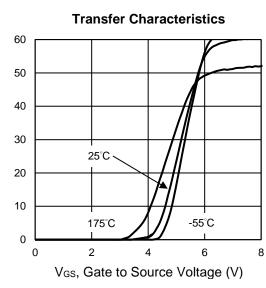


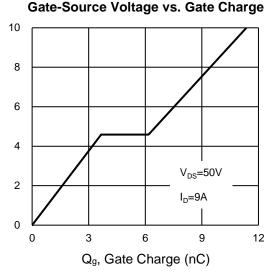
#### **CHARACTERISTICS CURVES**

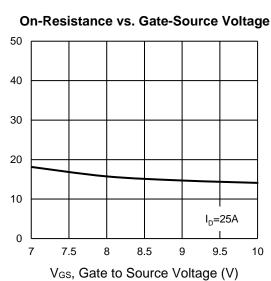
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



T<sub>J</sub>, Junction Temperature (°C)







3



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

0

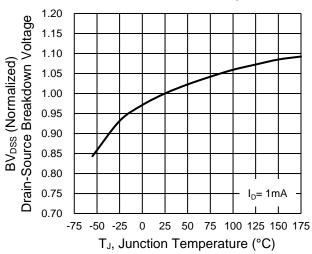
Normalized Effective Transient

Thermal Impedance, Zeuc



1000 Ciss Ciss Coss Coss Crss Crss Crss The state of the

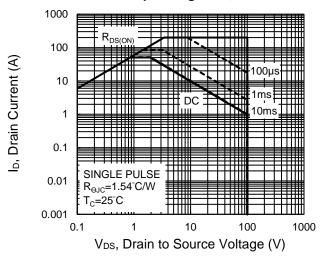
# BV<sub>DSS</sub> vs. Junction Temperature



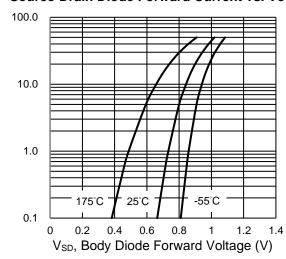
#### Maximum Safe Operating Area, Junction-to-Case

V<sub>DS</sub>, Drain to Source Voltage (V)

100



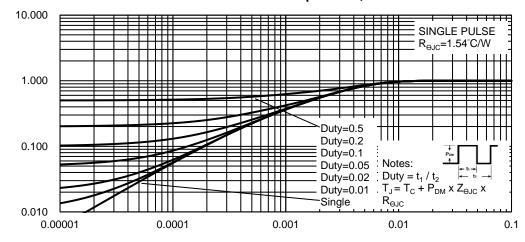
Source-Drain Diode Forward Current vs. Voltage



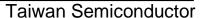
#### Normalized Thermal Transient Impedance, Junction-to-Case

Reverse Drain Current (A)

<u>,</u>



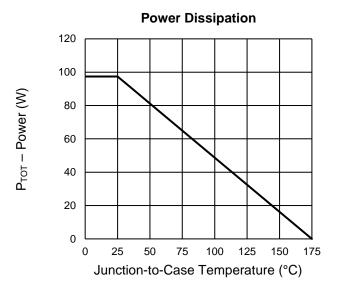
t, Square Wave Pulse Duration (sec)

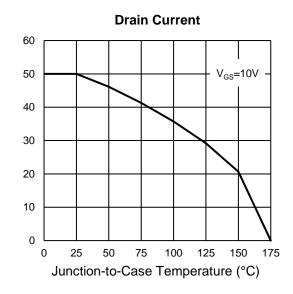




#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

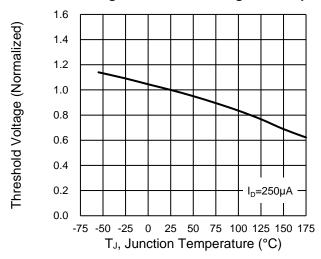


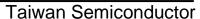


I<sub>D</sub>-Drain Current (A)

5

#### Normalized gate threshold voltage vs Temperature

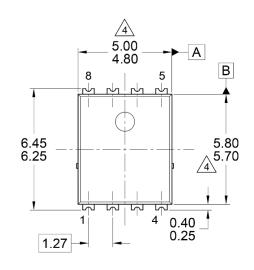


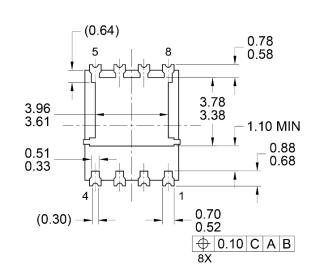


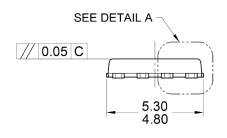


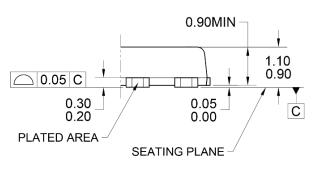
### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

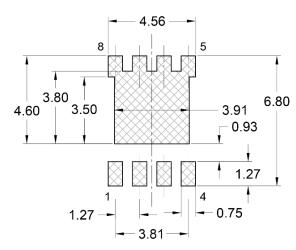
#### PDFN56U







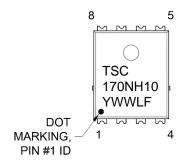




SUGGESTED PAD LAYOUT

(REFERENCE ONLY)

DETAIL A (SCALE 2:1)



#### NOTES: UNLESS OTHERWISE SPECIFIED

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1. ALL DIMENSIONS ARE IN MILLIMETERS.

- 170NH10 = Device marking
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- Y = Year code WW = Week code (01~52)

MARKING DIAGRAM

3. PACKAGE OUTLINE REFERENCE: JEITA ED-7500B, EIAJ SC-111BB.

L = Lot code  $(1\sim9,A\sim Z)$ F = Factory code

MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

5. DWG NO. REF: HQ2SD07-PDFN56U-023 REV B.



Taiwan Semiconductor

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